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2002 06 22

(21) 10 - 1993 - 0021946
(22) 1993 10 21

(65) 1995 - 0012900
(43) 1995 05 17

(73) 3 416

(72) 56 - 5

(74)

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(54)

InGaP, InGaP, InGaAIP, V, InGaAIP, InGaP, V, InGaP, InGaP, GaInP, p - GaAs, P - InGaAIP, p - GaInP

1

1

2

3 5

(He - Ne) , (Ar) (單光性), YAG 가 (CDP) 가

가

P - N (Quantum Electron)

(Metal Organic Chemical Vapor Deposition; MOCVD) (Liquid Phase Epitaxy; LPE) MBE (Molecular Beam Epitaxy) (Epitaxial) 가

가 가

(Optical Power) VSIS (V - c channel substrate inner stripe) 1

(3) p - (8) p - GaAs (1) p - GaAs (2) n - GaAs (6: V) n - GaAs (7) p - AlGaInP (4:), GaInP (5), n - AlGaInP (9) n - GaAs (7) n -

aAs (2) n - GaAs () (3) p - GaAs (1) p - G (MOCVD) 1

p - GaAs (2) n - GaAs (3) V
 (6) n - GaAs (7) V p - AlGaInP (4), GaInP (5), n - AlGaInP (MOCVD) 2
 (MBE)
 가 VSIS 2 () V 가 가 2 V
 , , 가 가 (1 : a)
 가
 p - GaAs p - AlGaInP P - P 가
 (spike)
 , V V 2 1 V
 가 , 2
 ,
 InGaP ;
 InGaP V InGaAIP ;
 V InGaAIP ;
 InGaAIP InGaP ;
 InGaP InGaAIP
 InGaP p - InGaP 가 InGaAIP 가
 2
 p (30) p - GaAs (10) V p - InGaP (20) n - InGaAIP
 nP (50) V (50) n - InGaAIP p - AlGaInP (60) n - GaAs (40) Gal (70)

, p - InGaP (20) GaInP (10) InGaAIP (40) 가 InGaAIP
 p - InGaAIP (30) p - InGaAIP (40) GaInP (50)

가 GaInP GaAs InGaAIP 가 (30)

p - GaInP (20) p - GaAs (10) p - InGaAIP (40) 가
 (spike)

50) V n - InGaAIP (30) p - InGaAIP (40) InGaP (40)
 (40) (50)

VSIS 가

3 5

3 (10) p - InGaP (20) n - InGaAIP (30) 1
 ()

4 (20) (30)
 V

, 5 V (30) p - InGaAIP (40) GaInP (50) n - InGaAIP (60) n - GaAs (70)

GaInP GaAs InGaAIP 가 (30) 가 가

p - GaInP (20) p - GaAs (10) p - InGaAIP (40) 가
 (spike)

(50) V n - InGaAIP (30) p - InGaAIP (40) InGaP (40)
 (40) (50)

가

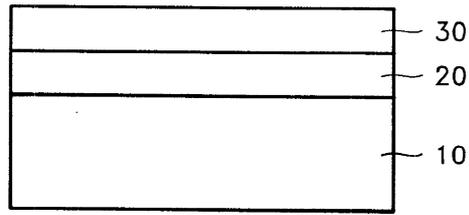
가

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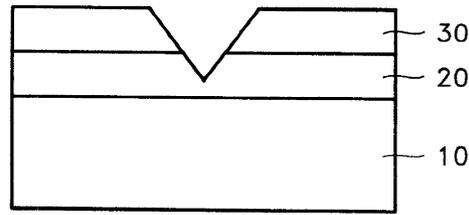
1.

InGaP ;

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